

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

241072US2SRD

SERIAL NO.

10/629,624

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Naoki SHUTOH, et al.

FILING DATE

July 30, 2003

GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
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FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
ADF	AO	2001-189495	07/10/2001	JAPAN		X
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	AV					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

ADF	AW	H. HOHL, et al., J. Phys.: Condens., matter 11, pages 1697-1709, "EFFICIENT DOPANTS FOR ZrNiSn-BASED THERMOELECTRIC MATERIALS", 1999
ADF	AX	K. MASTRONARDI, et al., Applied Physics Letters, vol. 74, no. 10, pages 1415-1417, "ANTIMONIDES WITH THE HALF-HEUSLER STRUCTURE: NEW THERMOELECTRIC MATERIALS", March 8, 1999
	AY	
	AZ	

☐ Additional References sheet(s) attached

Examiner

/Anthony Fick/ ADF

Date Considered

01/19/2007

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



LIST OF RELATED CASES

	<u>Docket Number</u>	<u>Serial or Patent Number</u>	<u>Filing or Issue Date</u>	<u>Inventor/ Applicant</u>
ADF	221292US2 SRD	10/105,341	03/26/02	SHUTOH et al.
ADF	241072US2 SRD*	10/629,624	07/30/03	SHUTOH et al.

ADF



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	<u>Docket Number</u>	<u>Serial or Patent Number</u>	<u>Filing or Issue Date</u>	<u>Patent Appl. Publication No.</u>	<u>Inventor/ Applicant</u>
ADF	241072US2SRD*	10/629,624	07/30/03		SHUTOH et al.
ADF	260012US2SRD	10/958,376	10/06/04		SHUTOH et al.

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ADF



SHEET 1 OF 1

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LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Naoki SHUTOH, et al.			
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ADF	AO	S. SPORTOUCH, et al., "Thermoelectric Properties of Half-Heusler Phases: $\text{ErNi}_{1-x}\text{Cu}_x\text{Sb}$, $\text{YbNi}_{1-x}\text{Cu}_x\text{Sb}$ And $\text{Zr}_2\text{Hf}_2\text{Ti}_2\text{NiSn}$ ", 18 th International Conference on Thermoelectrics Proceedings, ICT' 99, August 1999, pages 344-347					
ADF	AP	S. J. POON, et al., "Bandgap Features and Thermoelectric Properties of Ti-Based Half-Heusler Alloys" 18 th International Conferences on Thermoelectrics Proceedings, ICT' 99, August 1999, pages 45-51					
ADF	AQ	C. UHER, et al., "Thermoelectric Properties of Bi-Doped Half-Heusler Alloys", 18 th International Conference on Thermoelectrics Proceedings, ICT' 99, August 1999, pages 56-59					
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ADF	AS	Y. XIA, et al., "Thermoelectric Properties of semimetallic (Zr, Hf)CoSb half-Heusler phases", Journal of Applied Physics, vol. 88, no. 4, August 15, 2000, pages 1952-1955					
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ADF	AU	Q. SHEN, et al., "Effects of partial substitution of Ni by Pd on the thermoelectric properties of ZrNiSn-based half-Heusler compounds", Applied Physics Letters, vol. 79, no. 25, December 17, 2001, pages 4165-4167					
ADF	AV	Qiang SHEN, et al., "Thermoelectric Properties of ZrNiSn-based half-Heusler compounds by solid state reaction method", Journal of Materials Science Letters, vol. 20, no. 24, December 2001, pages 2197-2199					
ADF	AW	S. Joseph POON, et al., "Electronic and Thermoelectric Properties of Half-Heusler Alloys", Semiconductors and Semimetals, Academic Press, vol. 70, 2001, pages 37-75					
ADF	AX	Shen QIANG, et al., "Synthesis and Thermoelectric Properties of ZrNiSn-based Semi-Heusler Compounds, Preprints of Annual Meeting of The Ceramic Society of Japan, March 21, 2001, page 285					<input type="checkbox"/> Additional References sheet(s) attached
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